

Vishay Semiconductors

AUTOMOTIVE

RoHS

COMPLIANT HALOGEN

FREE

# **Ultrafast Rectifier, 2 A FRED Pt®**

# eSMP<sup>®</sup> Series





Top View Bottom View

MicroSMP (DO-219AD)

Anode O Cathode

### **LINKS TO ADDITIONAL RESOURCES**



| PRIMARY CHARACTERISTICS          |                     |  |  |  |
|----------------------------------|---------------------|--|--|--|
| I <sub>F(AV)</sub>               | 2 A                 |  |  |  |
| V <sub>R</sub>                   | 100 V, 200 V        |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.82 V              |  |  |  |
| t <sub>rr</sub> (typ.)           | 33 ns               |  |  |  |
| I <sub>FSM</sub>                 | 30 A                |  |  |  |
| T <sub>J</sub> max.              | 175 °C              |  |  |  |
| Package                          | MicroSMP (DO-219AD) |  |  |  |
| Circuit configuration            | Single              |  |  |  |

#### **FEATURES**

- Very low profile typical height of 0.65 mm
- · Ideal for automated placement
- · Low forward voltage drop, low power losses
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- For PFC, CRM snubber operation
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### TYPICAL APPLICATIONS

For use in high frequency, freewheeling, DC/DC converters, PFC, and in snubber industrial and automotive applications.

#### **MECHANICAL DATA**

Case: MicroSMP (DO-219AD)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per

J-STD-002, meets JESD 201 class 2 whisker test

Polarity: color band denotes cathode end

| ABSOLUTE MAXIMUM RATINGS                     |                                   |                                 |             |       |  |  |  |
|--|-----------------------------------|---------------------------------|-------------|-------|--|--|--|
| PARAMETER                                    | SYMBOL                            | TEST CONDITIONS                 | VALUES      | UNITS |  |  |  |
| Peak repetitive reverse voltage VS-2EQH01HM3 | - V <sub>RRM</sub>                |                                 | 100         | V     |  |  |  |
| VS-2EQH02HM3                                 |                                   |                                 | 200         |       |  |  |  |
| Average rectified forward current            | I <sub>F(AV)</sub>                | T <sub>M</sub> = 137 °C         | 2           | ۸     |  |  |  |
| Non-repetitive peak surge current            | I <sub>FSM</sub>                  | $T_J = 25$ °C, 10 ms sine pulse | 30          | A     |  |  |  |
| Operating junction and storage temperatures  | T <sub>J</sub> , T <sub>Stg</sub> |                                 | -55 to +175 | °C    |  |  |  |

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                |                      |  |      |      |      |       |
|--|----------------|----------------------|--|------|------|------|-------|
| PARAMETER  |                | SYMBOL               | TEST CONDITIONS  | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage,   | VS-2EQH01HM3   | $V_{BR}$ ,           | I <sub>R</sub> = 100 μA                                | 100  | -    | -    |       |
| blocking voltage   | VS-2EQH02HM3   | $V_R$                |  | 200  |      |      | V     |
| Farmer de la la cara   | V              | I <sub>F</sub> = 2 A | -  | 0.96 | 1.05 | V    |       |
| Forward voltage  | orward voltage | V <sub>F</sub>       | I <sub>F</sub> = 2 A, T <sub>J</sub> = 150 °C          | -    | 0.82 | 0.84 |       |
| Reverse leakage current  |                | ,                    | V <sub>R</sub> = V <sub>R</sub> rated                  | -    | -    | 1    |       |
|  |                | IR                   | $T_J = 150 ^{\circ}\text{C},  V_R = V_R  \text{rated}$ | -    | -    | 25   | μA    |
| Junction capacitance   |                | C <sub>T</sub>       | V <sub>R</sub> = 200 V                                 | -    | 6    | -    | pF    |

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| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                         |   |                      |      |      |      |         |
|---|-------------------------|---|----------------------|------|------|------|---------|
| PARAMETER   | SYMBOL                  | TEST CONDITIONS   |                      | MIN. | TYP. | MAX. | UNITS   |
|   |                         | $I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ |                      | -    | 33   | -    |         |
| Reverse recovery time t <sub>rr</sub>   |                         | I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A        |                      | -    | -    | 23   |         |
|   | ιm                      | T <sub>J</sub> = 25 °C  | I <sub>F</sub> = 2 A | -    | 19   | -    | ns<br>A |
|   |                         | T <sub>J</sub> = 125 °C   |                      | -    | 33   | -    |         |
| Peak recovery current I <sub>RRM</sub>  | ,                       | T <sub>J</sub> = 25 °C  |                      | -    | 1.7  | -    |         |
|   | T <sub>J</sub> = 125 °C | $dI_F/dt = 200 \text{ A/}\mu\text{s}$<br>$V_R = 100 \text{ V}$                | -                    | 2.5  | -    | _ ^  |         |
| Reverse recovery charge Q <sub>rr</sub>   | T <sub>J</sub> = 25 °C  |   | -                    | 15   | -    | nC   |         |
|   | T <sub>J</sub> = 125 °C |   | -                    | 34   | -    | TIC  |         |

| THERMAL - MECHANICAL SPECIFICATIONS     |                     |                                   |   |      |       |      |       |
|---|---------------------|-----------------------------------|---|------|-------|------|-------|
| PARAMETER                               |                     | SYMBOL                            | TEST CONDITIONS                                     | MIN. | TYP.  | MAX. | UNITS |
| Maximum junction and range              | storage temperature | T <sub>J</sub> , T <sub>Stg</sub> |   | -55  | -     | 175  | °C    |
| Thermal resistance, junction to mount   |                     | R <sub>thJM</sub> <sup>(1)</sup>  |   | -    | 16    | 20   |       |
| Thermal resistance, junction to ambient |                     | R <sub>thJA</sub>                 | Device mounted on FR4 PCB, 2 oz. standard footprint | -    | 160   | -    | °C/W  |
| Approximate weight                      |                     |                                   |   |      | 0.006 |      | g     |
| Marking device                          | VS-2EQH01HM3        |                                   | Case style MicroSMP (DO-219AD)                      | 2H1  |       |      | •     |
| iviai kirig device                      | VS-2EQH02HM3        |                                   | Case style MicrosMP (DO-219AD)                      |      | 2H2   |      | •     |

#### Note

<sup>(1)</sup> Thermal resistance junction to mount follows JEDEC® 51-14 transient dual interface test method (TDIM)

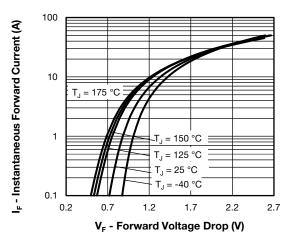


Fig. 1 - Typical Forward Voltage Drop Characteristics

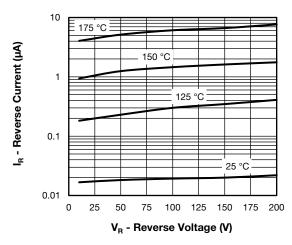


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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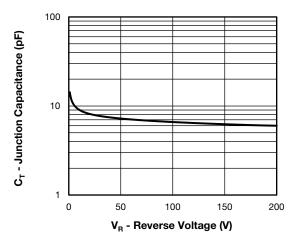


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

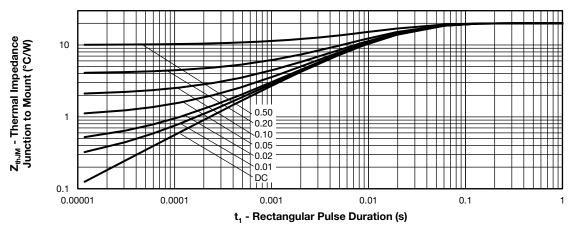


Fig. 4 - Maximum Transient Thermal Impedance, Junction to Mount

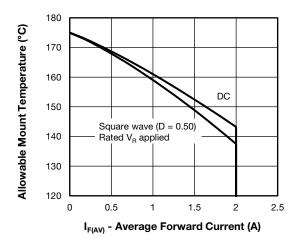


Fig. 5 - Maximum Allowable Mount Temperature vs. Average Forward Current

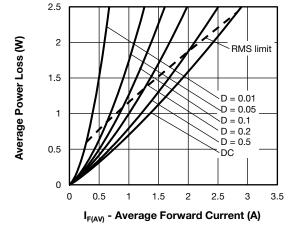
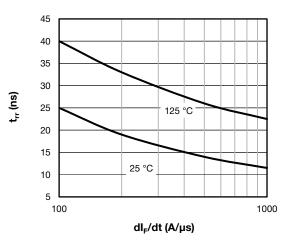


Fig. 6 - Forward Power Loss Characteristics

#### Note

Formula used:  $T_M = T_J - (Pd + Pd_{REV}) \times R_{thJM}$ ;  $Pd = forward power loss = I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 5);  $Pd_{REV} = inverse power loss = V_{R1} \times I_R$  (1 - D);  $I_R$  at  $V_{R1} = rated V_R$ 

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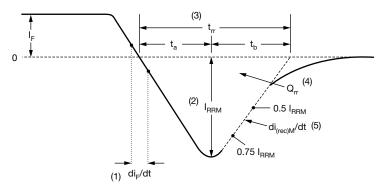


45 40 35 30 35 25 20 15 100 1000 dl<sub>F</sub>/dt (A/μs)

50

Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) di<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RRM</sub> and 0.50 I<sub>RRM</sub> extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

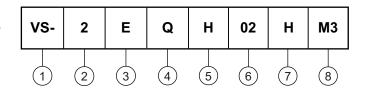
(5) di<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

**Device code** 



1 - Vishay Semiconductors product

2 - Current rating (2 = 2 A)

- Circuit configuration:

E = single diode

4 - Q = MicroSMP package

5 - Process type,

H = ultrafast recovery

6 - Voltage code (02 = 200 V)

7 - H = AEC-Q101 qualified

8 - M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example)  |   |      |                                   |  |  |  |
|---|---|------|-----------------------------------|--|--|--|
| PREFERRED P/N PREFERRED PACKAGE CODE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION |   |      |                                   |  |  |  |
| VS-2EQH01HM3/H  | Н | 4500 | 7" diameter plastic tape and reel |  |  |  |
| VS-2EQH02HM3/H  | Н | 4500 | 7" diameter plastic tape and reel |  |  |  |

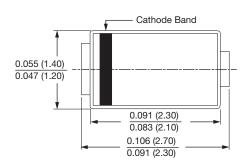
| LINKS TO RELATED DOCUMENTS                 |                          |  |  |  |
|--|--------------------------|--|--|--|
| Dimensions <u>www.vishay.com/doc?96591</u> |                          |  |  |  |
| Part marking information                   | www.vishay.com/doc?96590 |  |  |  |
| Packaging information                      | www.vishay.com/doc?88869 |  |  |  |
| SPICE model                                | www.vishay.com/doc?96595 |  |  |  |

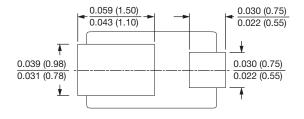


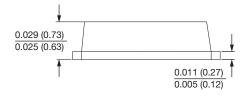
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# MicroSMP (DO-219AD), FRED Pt®

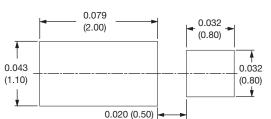
### **DIMENSIONS** in inches (millimeters)







### Mounting Pad Layout





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